

## -20V P-Channel Enhancement Mode MOSFET

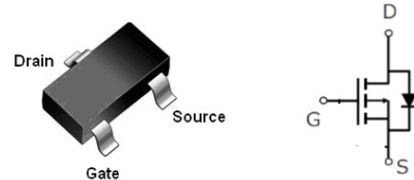
### Features

- Low  $R_{DS(on)}$  @  $V_{GS} = -4.5V$
- -3.3V Logic Level Control
- P Channel SOT23 Package
- Pb-Free, RoHS Compliant

| $V_{(BR)DSS}$ | $R_{DS(ON)}$ Typ     | $I_D$ Max |
|---------------|----------------------|-----------|
| -20V          | 115m $\Omega$ @ 4.5V | -2.3A     |
|               | 140m $\Omega$ @ 3.3V |           |

### Applications

- High-side Load Switch
- Switching Circuits
- High Speed line Driver



### Order Information

**SOT23**

| Product    | Package | Marking | Packing      |
|------------|---------|---------|--------------|
| AM20DP023M | SOT23   | A1SHB   | 3000PCS/Reel |

### Absolute Maximum Ratings

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

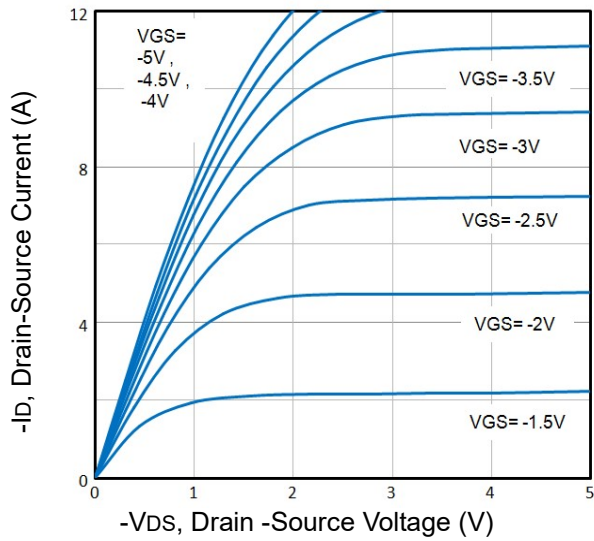
| Symbol                                                       | Parameter                           |                      | Rating     | Unit |
|--------------------------------------------------------------|-------------------------------------|----------------------|------------|------|
| Common Ratings (T <sub>A</sub> =25°C Unless Otherwise Noted) |                                     |                      |            |      |
| V <sub>GS</sub>                                              | Gate-Source Voltage                 |                      | ±10        | V    |
| V <sub>(BR)DSS</sub>                                         | Drain-Source Breakdown Voltage      |                      | -20        | V    |
| T <sub>J</sub>                                               | Maximum Junction Temperature        |                      | 150        | °C   |
| T <sub>STG</sub>                                             | Storage Temperature Range           |                      | -50 to 150 | °C   |
| Mounted on Large Heat Sink                                   |                                     |                      |            |      |
| I <sub>DM</sub>                                              | Pulse Drain Current Tested①         | T <sub>A</sub> =25°C | -9         | A    |
| I <sub>D</sub>                                               | Continuous Drain Current            | T <sub>A</sub> =25°C | -2.3       | A    |
|                                                              |                                     | T <sub>A</sub> =70°C | -2.0       |      |
| P <sub>D</sub>                                               | Maximum Power Dissipation           | T <sub>A</sub> =25°C | 1          | W    |
|                                                              |                                     | T <sub>A</sub> =70°C | 0.8        |      |
| R <sub>θJA</sub>                                             | Thermal Resistance Junction-Ambient |                      | 125        | °C/W |

| Symbol                                                                               | Parameter                                              | Condition                                                                                         | Min  | Typ   | Max  | Unit |
|--------------------------------------------------------------------------------------|--------------------------------------------------------|---------------------------------------------------------------------------------------------------|------|-------|------|------|
| Static Electrical Characteristics @ T <sub>J</sub> = 25°C (unless otherwise stated)  |                                                        |                                                                                                   |      |       |      |      |
| V <sub>(BR)DSS</sub>                                                                 | Drain-Source Breakdown Voltage                         | V <sub>GS</sub> =0V I <sub>D</sub> =-250μA                                                        | -20  | --    | --   | V    |
| I <sub>DSS</sub>                                                                     | Zero Gate Voltage Drain Current(T <sub>A</sub> =25°C)  | V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V                                                        | --   | --    | -1   | μA   |
|                                                                                      | Zero Gate Voltage Drain Current(T <sub>A</sub> =125°C) | V <sub>DS</sub> =-16V, V <sub>GS</sub> =0V                                                        | --   | --    | -100 | uA   |
| I <sub>GSS</sub>                                                                     | Gate-Body Leakage Current                              | V <sub>GS</sub> =±10V, V <sub>DS</sub> =0V                                                        | --   | --    | ±100 | nA   |
| V <sub>GS(TH)</sub>                                                                  | Gate Threshold Voltage                                 | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA                                         | -0.4 | -0.6  | -1.0 | V    |
| R <sub>DS(ON)</sub>                                                                  | Drain-Source On-State Resistance②                      | V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2A                                                       | --   | 115   | 138  | mΩ   |
| R <sub>DS(ON)</sub>                                                                  | Drain-Source On-State Resistance②                      | V <sub>GS</sub> =-3.3V, I <sub>D</sub> =-1A                                                       | --   | 140   | 170  | mΩ   |
| R <sub>DS(ON)</sub>                                                                  | Drain-Source On-State Resistance②                      | V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-1A                                                       | --   | 170   | 210  | mΩ   |
| Dynamic Electrical Characteristics @ T <sub>J</sub> = 25°C (unless otherwise stated) |                                                        |                                                                                                   |      |       |      |      |
| C <sub>iss</sub>                                                                     | Input Capacitance                                      | V <sub>DS</sub> =-10V, V <sub>GS</sub> =0V,<br>f=1MHz                                             | --   | 177   | --   | pF   |
| C <sub>oss</sub>                                                                     | Output Capacitance                                     |                                                                                                   | --   | 30    | --   | pF   |
| C <sub>rss</sub>                                                                     | Reverse Transfer Capacitance                           |                                                                                                   | --   | 25    | --   | pF   |
| Q <sub>g</sub>                                                                       | Total Gate Charge                                      | V <sub>DS</sub> =-10V<br>I <sub>D</sub> =-2A,<br>V <sub>GS</sub> =-4.5V                           | --   | 5.3   | --   | nC   |
| Q <sub>gs</sub>                                                                      | Gate Source Charge                                     |                                                                                                   | --   | 0.7   | --   | nC   |
| Q <sub>gd</sub>                                                                      | Gate Drain Charge                                      |                                                                                                   | --   | 1.4   | --   | nC   |
| Switching Characteristics                                                            |                                                        |                                                                                                   |      |       |      |      |
| t <sub>d(on)</sub>                                                                   | Turn on Delay Time                                     | V <sub>DD</sub> =-10V,<br>I <sub>D</sub> =-2A,<br>R <sub>G</sub> =3.3Ω,<br>V <sub>GS</sub> =-4.5V | --   | 11    | --   | ns   |
| t <sub>r</sub>                                                                       | Turn on Rise Time                                      |                                                                                                   | --   | 32    | --   | ns   |
| t <sub>d(off)</sub>                                                                  | Turn Off Delay Time                                    |                                                                                                   | -    | 25    | --   | ns   |
| t <sub>f</sub>                                                                       | Turn Off Fall Time                                     |                                                                                                   | --   | 38    | --   | ns   |
| Source Drain Diode Characteristics                                                   |                                                        |                                                                                                   |      |       |      |      |
| I <sub>SD</sub>                                                                      | Source drain current(Body Diode)                       | T <sub>A</sub> =25°C                                                                              | --   | --    | -1.2 | A    |
| V <sub>SD</sub>                                                                      | Forward on voltage②                                    | T <sub>J</sub> =25°C, I <sub>SD</sub> =-1A,<br>V <sub>GS</sub> =0V                                | --   | -0.83 | -1.2 | V    |

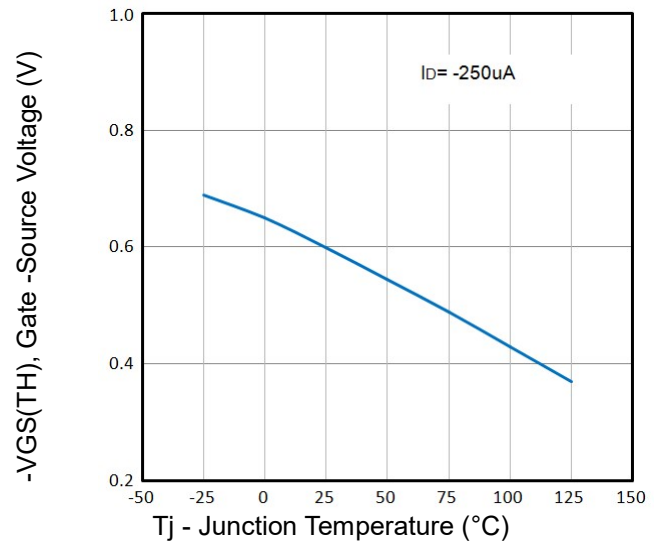
Notes:

- ① Pulse width limited by maximum allowable junction temperature
- ② Pulse test ; Pulse width≤300μs, duty cycle≤2%.

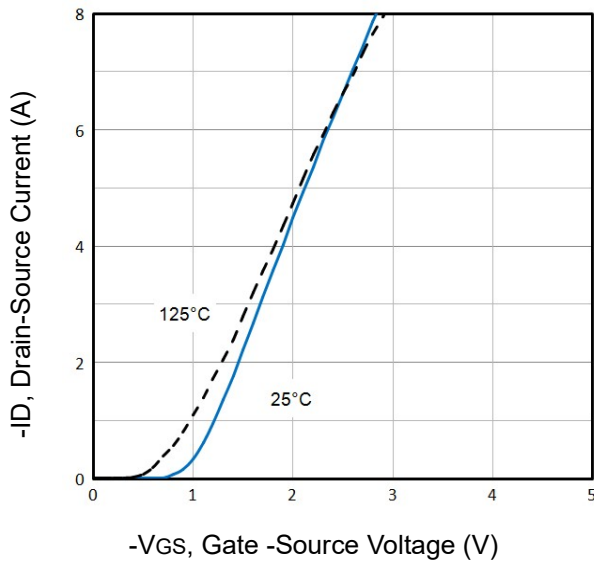
## Typical Characteristics



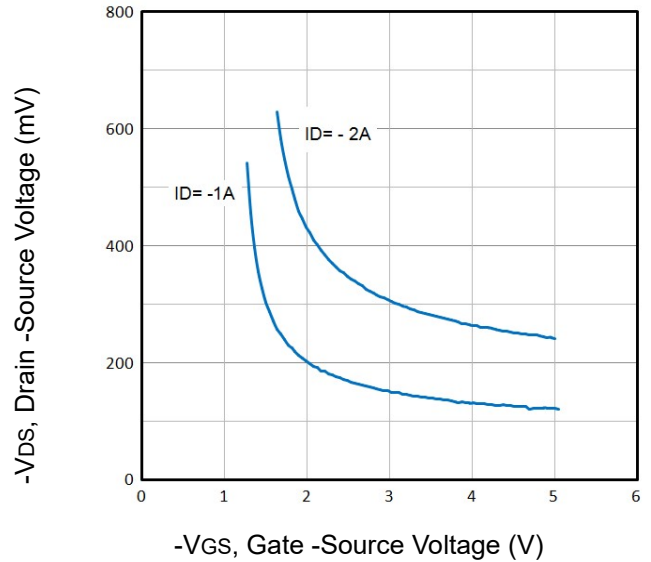
**Fig1.** Typical Output Characteristics



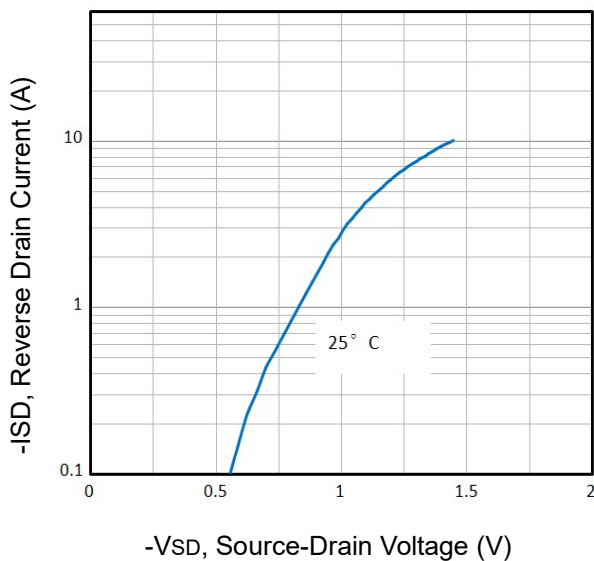
**Fig2.** Normalized Threshold Voltage Vs. Temperature



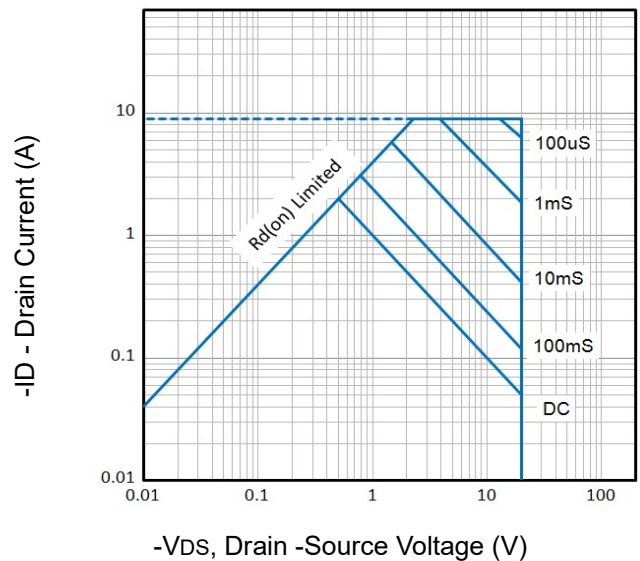
**Fig3.** Typical Transfer Characteristics



**Fig4.** Drain -Source Voltage vs Gate -Source Voltage

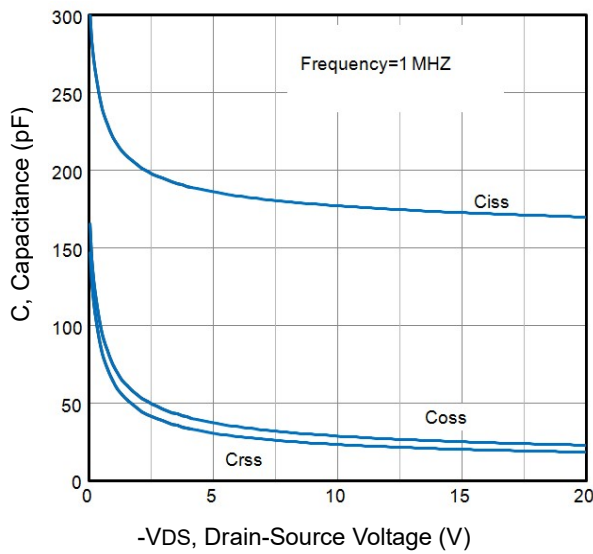


**Fig5.** Typical Source-Drain Diode Forward Voltage

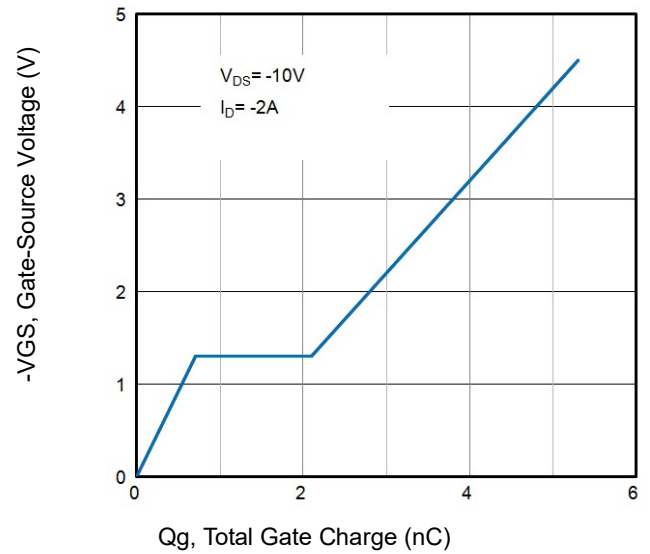


**Fig6.** Maximum Safe Operating Area

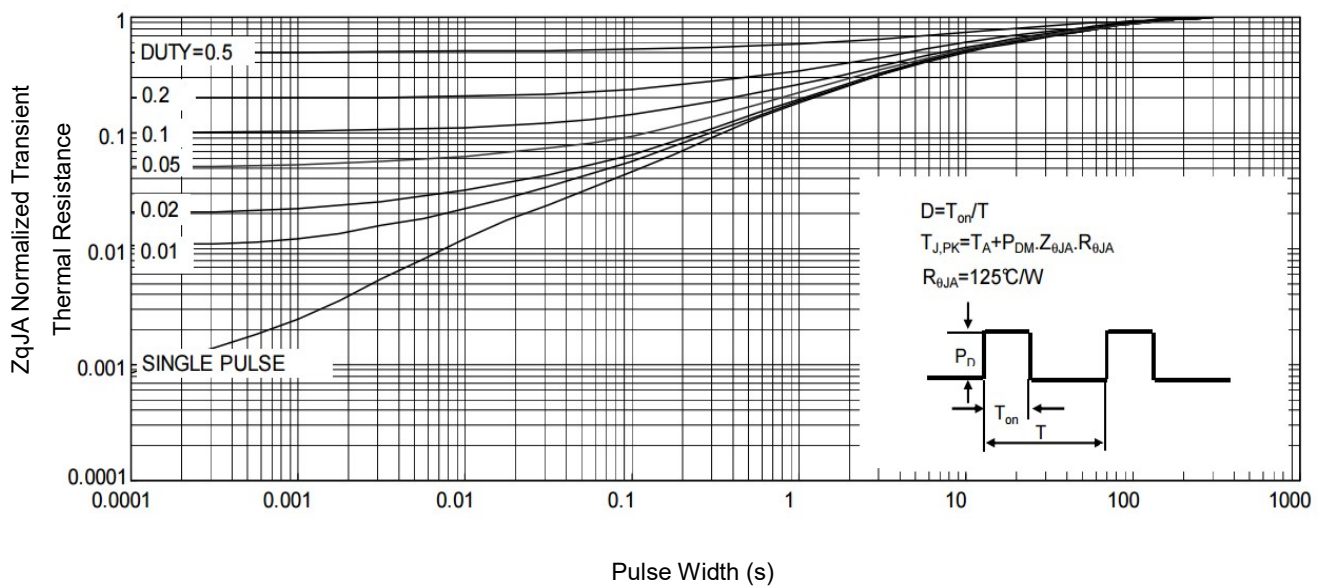
## Typical Characteristics



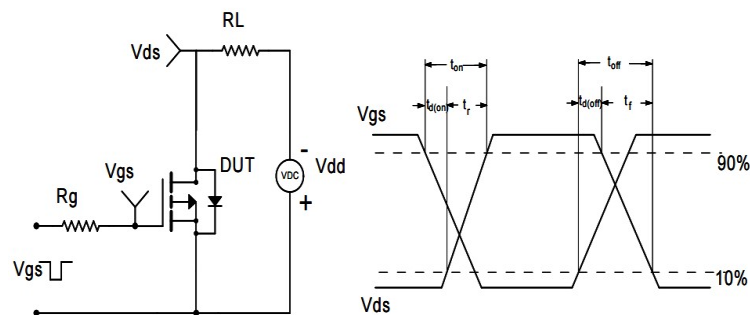
**Fig7.** Typical Capacitance Vs. Drain-Source Voltage



**Fig8.** Typical Gate Charge Vs. Gate-Source Voltage

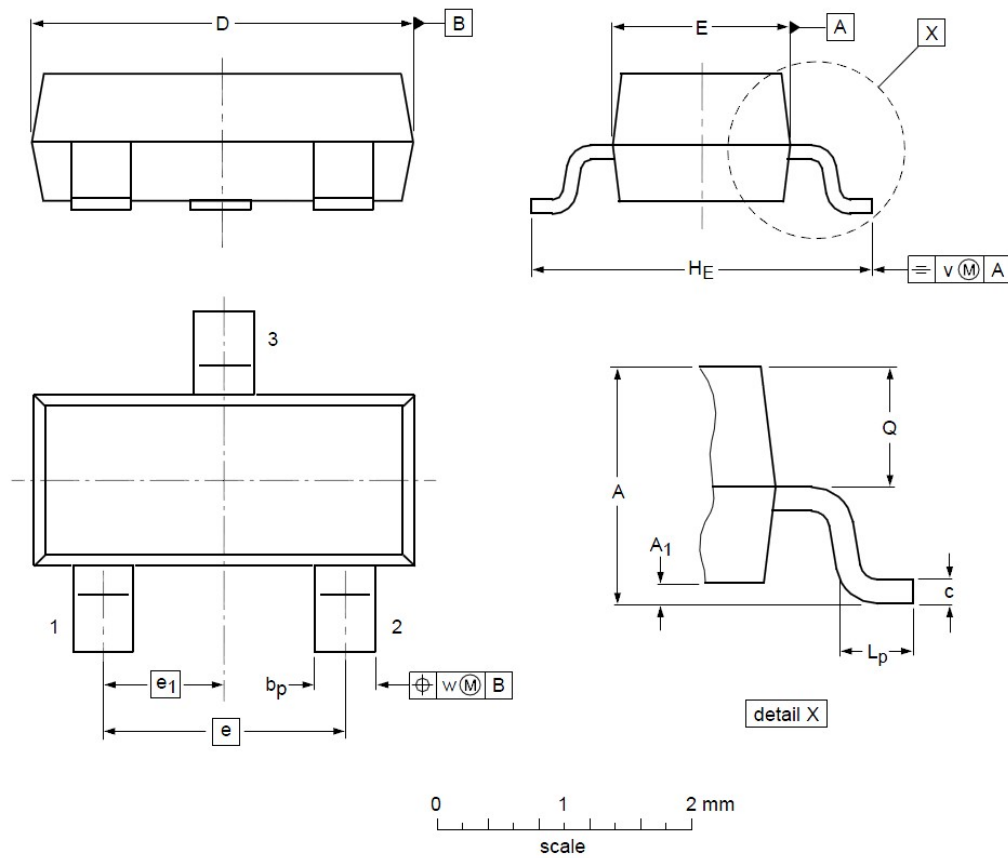


**Fig9.** Normalized Maximum Transient Thermal Impedance



**Fig10.** Switching Time Test Circuit and waveforms

## SOT23 Mechanical Data



**DIMENSIONS** ( unit : mm )

| Symbol               | Min  | Typ  | Max  | Symbol               | Min  | Typ  | Max  |
|----------------------|------|------|------|----------------------|------|------|------|
| <b>A</b>             | 0.90 | 1.01 | 1.15 | <b>A<sub>1</sub></b> | 0.01 | 0.05 | 0.10 |
| <b>b<sub>p</sub></b> | 0.30 | 0.42 | 0.50 | <b>c</b>             | 0.08 | 0.13 | 0.15 |
| <b>D</b>             | 2.80 | 2.92 | 3.00 | <b>E</b>             | 1.20 | 1.33 | 1.40 |
| <b>e</b>             | --   | 1.90 | --   | <b>e<sub>1</sub></b> | --   | 0.95 | --   |
| <b>H<sub>E</sub></b> | 2.25 | 2.40 | 2.55 | <b>L<sub>p</sub></b> | 0.30 | 0.42 | 0.50 |
| <b>Q</b>             | 0.45 | 0.49 | 0.55 | <b>v</b>             | --   | 0.20 | --   |
| <b>w</b>             | --   | 0.10 | --   |                      |      |      |      |

## SOT-23 Suggested Pad Layout

